# MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet



#### **Feature**

- > 80W peak pulse power per line ( $t_P = 8/20\mu s$ )
- > DFN1006 package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns</p>
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC61000-4-4 (EFT) 40A (5/50ns)

#### **Applications**

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

#### **Mechanical Characteristics**

- Mounting position: Any
- > Qualified max reflow temperature:260°C
- > Device meets MSL 1 requirements
- DFN1006-2L without plating

## Absolute maximum rating@25°C

**DFN1006** 

**PIN CONFIGURATION** 

Rating	Symbol	Value	Units
Peak Pulse Power (t <sub>p</sub> =8/20μs)	P <sub>pp</sub>	80	W
Peak Pulse Current (t <sub>p</sub> =8/20μs)	I <sub>pp</sub>	8	А
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

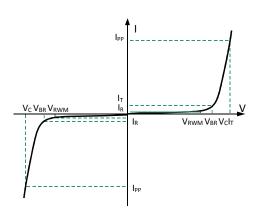
#### Electrical characteristics per line@25°C (unless otherwisespecified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				5	V
Breakdown Voltage	$V_{BR}$	I <sub>t</sub> = 1mA	5.6	7.0	7.8	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 5V T=25°C			1.0	μA
Clamping Voltage	V <sub>CL</sub>	I <sub>PP</sub> =16A t <sub>p</sub> =100ns		10.5		V
Clamping Voltage	Vc	I <sub>PP</sub> =1A		7.5	8.0	V
Clamping Voltage	Vc	I <sub>PP</sub> =3A		8.0	9.0	V
Clamping Voltage	Vc	I <sub>PP</sub> =8A		8.5	10	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		30		pF

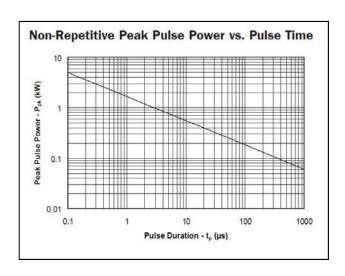


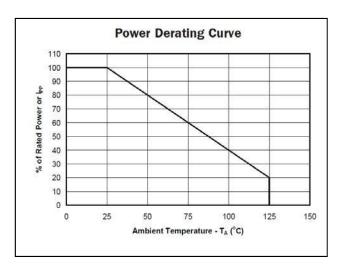
#### **Electronics Parameter**

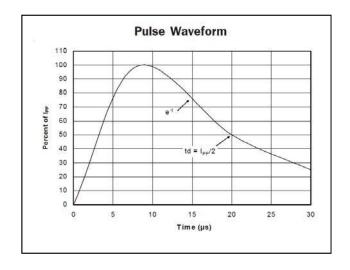
Symbol	Parameter		
V <sub>RWM</sub>	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
V <sub>BR</sub>	Breakdown Voltage @ I⊤		
Ι <sub>Τ</sub>	Test Current		
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
V <sub>C</sub>	Clamping Voltage @ IPP		
P <sub>PP</sub>	Peak Pulse Power		
CJ	Junction Capacitance		

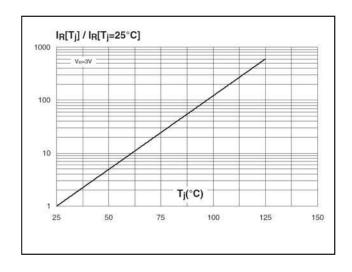


# Typical Characteristics@ Ta=25°C unless otherwise specified



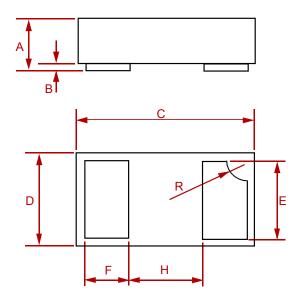






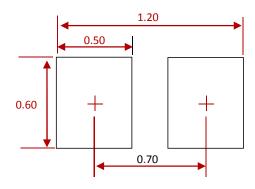






Direc	Inches		Millimeters		
Dim	MIN	MAX	MIN	MAX	
Α	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Typ.		
R	0.001	0.005	0.05	0.15	

# **Suggested Pad Layout**



#### NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MSAZ5825-01F	DFN1006	10000



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